

## General Description

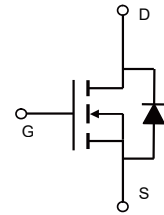
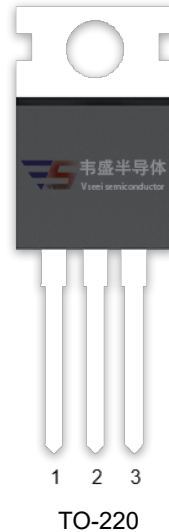
The series of devices use advanced trench gate super junction technology and design to provide ultra-low  $R_{DS(ON)}$  and low gate charge and With a rapid recovery body diode. This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, industrial power applications, Fast charger, new energy vehicle charging pile, on-board OBC etc.

## Features

- New technology for high voltage device
- Ultra low on-resistance and ultra low conduction losses
- Ultra Low Gate Charge cause lower driving requirements
- Diode reverse recovery speed is super fast
- High reliability
- ROHS compliant

## Application

- Power factor correction (PFC)
- Switched mode power supplies(SMPS)
- Uninterruptible Power Supply (UPS)
- On-board charger(OBC)



Schematic

| Parameter                                                             | Symbol           | Value    | Unit          |
|-----------------------------------------------------------------------|------------------|----------|---------------|
| Drain-Source Voltage ( $V_{GS}=0V$ )                                  | $V_{DS}$         | 650      | V             |
| Gate-Source Voltage ( $V_{DS}=0V$ ) AC ( $f>1$ Hz)                    | $V_{GS}$         | $\pm 30$ | V             |
| Gate-Source Voltage ( $V_{DS}=0V$ ) DC                                | $V_{GS}$         | $\pm 20$ | V             |
| Continuous Drain Current at $T_c=25^\circ C$                          | $I_D (DC)$       | 36       | A             |
| Continuous Drain Current at $T_c=100^\circ C$                         | $I_D (DC)$       | 25.2     | A             |
| Pulsed drain current (Note 1)                                         | $I_{DM} (pluse)$ | 108      | A             |
| Maximum Power Dissipation( $T_c=25^\circ C$ )                         | $P_D$            | 346      | W             |
| Derate above $25^\circ C$                                             |                  | 2.30     | W/ $^\circ C$ |
| Single pulse avalanche energy (Note 2)                                | $E_{AS}$         | 324      | mJ            |
| Avalanche current(Note 1)                                             | $I_{AS}$         | 9        | A             |
| Repetitive Avalanche energy , $t_{AR}$ limited by $T_{jmax}$ (Note 1) | $E_{AR}$         | 3.9      | mJ            |

| Parameter                                                | Symbol         | Value      | Unit |
|----------------------------------------------------------|----------------|------------|------|
| Drain Source voltage slope, $V_{DS} \leq 480V$ ,         | $dv/dt$        | 50         | V/ns |
| Reverse diode $dv/dt$ , $V_{DS} \leq 480V, I_{SD} < I_D$ | $dv/dt$        | 50         | V/ns |
| Operating Junction and Storage Temperature Range         | $T_J, T_{STG}$ | -55...+175 | °C   |

\* limited by maximum junction temperature

**Table 2. Thermal Characteristic**

| Parameter                                         | Symbol     | Value | Unit  |
|---------------------------------------------------|------------|-------|-------|
| Thermal Resistance, Junction-to-Case (Maximum)    | $R_{thJC}$ | 0.43  | °C /W |
| Thermal Resistance, Junction-to-Ambient (Maximum) | $R_{thJA}$ | 62    | °C /W |

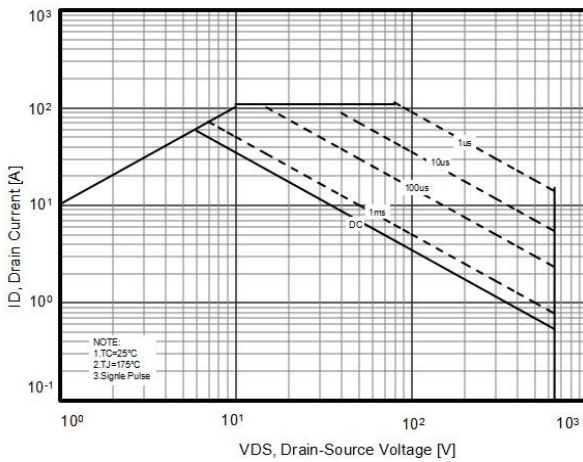
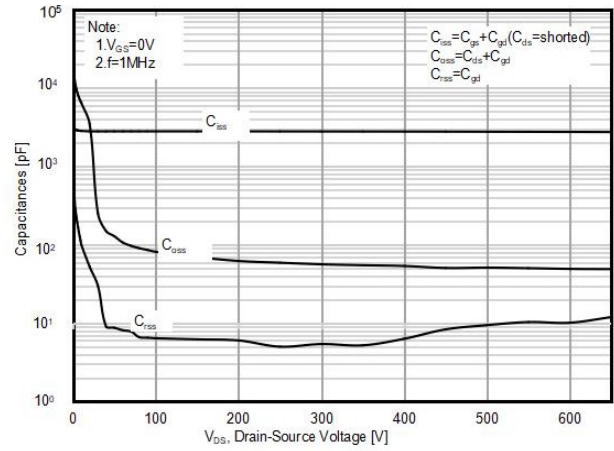
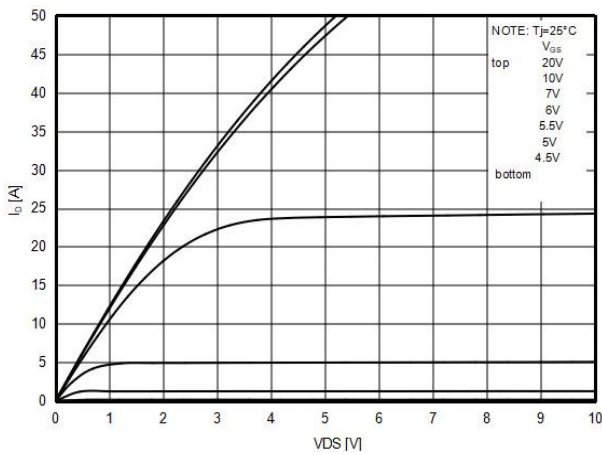
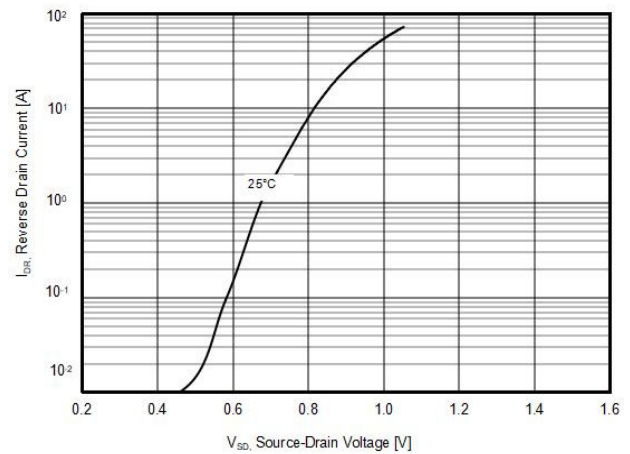
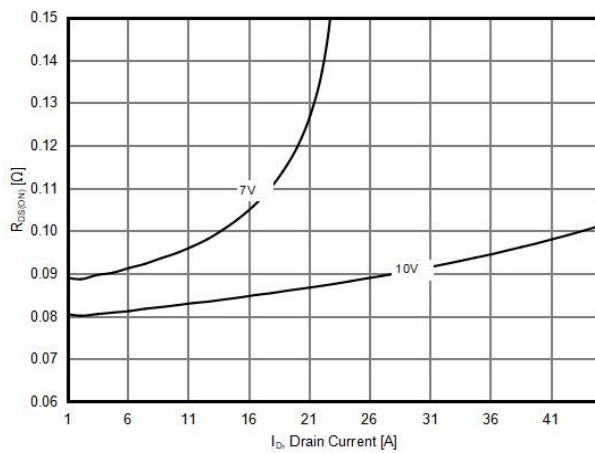
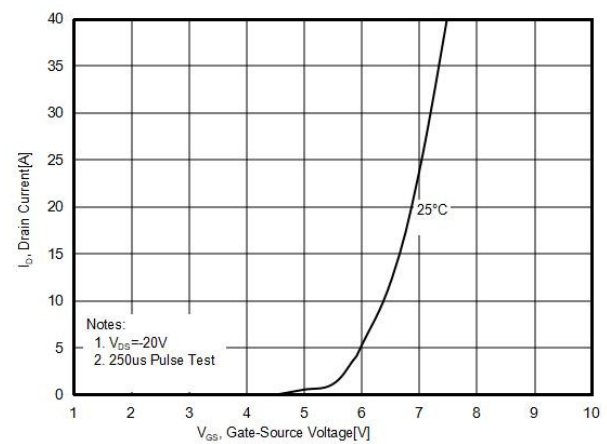
**Table 3. Electrical Characteristics (TA=25°C unless otherwise noted)**

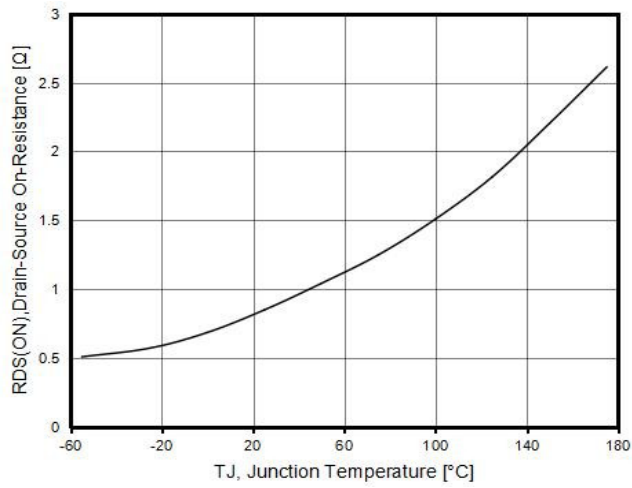
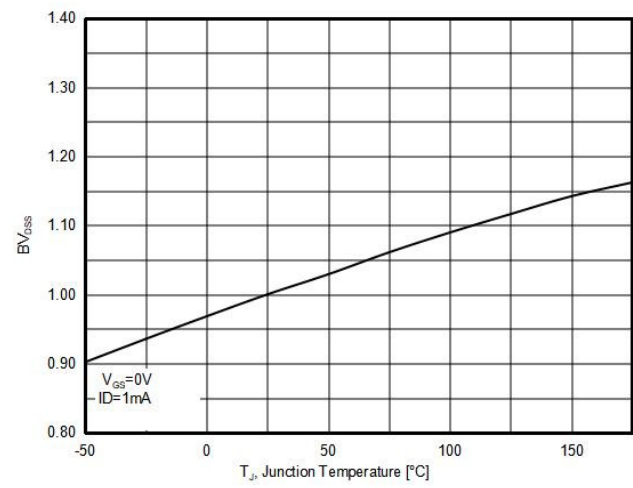
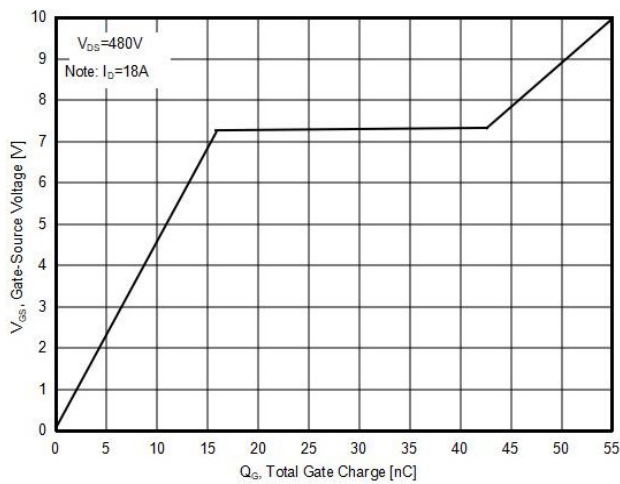
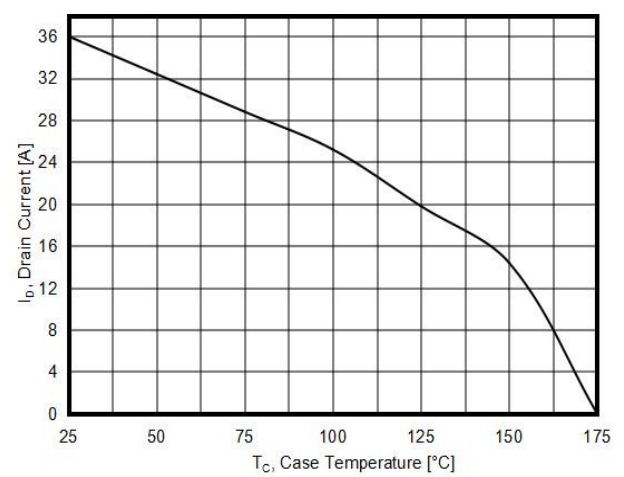
| Parameter                                | Symbol              | Condition                                                                                 | Min | Typ  | Max  | Unit |
|------------------------------------------|---------------------|-------------------------------------------------------------------------------------------|-----|------|------|------|
| On/off states                            |                     |                                                                                           |     |      |      |      |
| Drain-Source Breakdown Voltage           | BV <sub>DSS</sub>   | V <sub>GS</sub> =0V I <sub>D</sub> =1mA                                                   | 650 |      |      | V    |
| Zero Gate Voltage Drain Current(Tc=25℃)  | I <sub>DSS</sub>    | V <sub>DS</sub> =650V, V <sub>GS</sub> =0V                                                |     |      | 10   | μA   |
| Zero Gate Voltage Drain Current(Tc=125℃) | I <sub>DSS</sub>    | V <sub>DS</sub> =650V, V <sub>GS</sub> =0V                                                |     |      | 400  | μA   |
| Gate-Body Leakage Current                | I <sub>GSS</sub>    | V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V                                                |     |      | ±100 | nA   |
| Gate Threshold Voltage                   | V <sub>GS(th)</sub> | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =500uA                                  | 3.5 | 4.2  | 5.0  | V    |
| Drain-Source On-State Resistance         | R <sub>DS(ON)</sub> | V <sub>GS</sub> =10V, I <sub>D</sub> =18A                                                 |     | 85   | 99   | mΩ   |
| Dynamic Characteristics                  |                     |                                                                                           |     |      |      |      |
| Input Capacitance                        | C <sub>iss</sub>    | V <sub>DS</sub> =50V, V <sub>GS</sub> =0V,<br>F=1.0MHz                                    |     | 2800 | 3200 | pF   |
| Output Capacitance                       | C <sub>oss</sub>    |                                                                                           |     | 96   |      | pF   |
| Reverse Transfer Capacitance             | C <sub>rss</sub>    |                                                                                           |     | 6    |      | pF   |
| Total Gate Charge                        | Q <sub>g</sub>      | V <sub>DS</sub> =480V, I <sub>D</sub> =18A,<br>V <sub>GS</sub> =10V                       |     | 55   | 60   | nC   |
| Gate-Source Charge                       | Q <sub>gs</sub>     |                                                                                           |     | 16.5 |      | nC   |
| Gate-Drain Charge                        | Q <sub>gd</sub>     |                                                                                           |     | 25.5 |      | nC   |
| Gate plateau voltage                     | V <sub>gp</sub>     |                                                                                           |     | 7.3  |      | V    |
| Intrinsic gate resistance                | R <sub>G</sub>      | f = 1 MHz open drain                                                                      |     | 1.5  |      | Ω    |
| Switching times                          |                     |                                                                                           |     |      |      |      |
| Turn-on Delay Time                       | t <sub>d(on)</sub>  | V <sub>DD</sub> =380V, I <sub>D</sub> =18A,<br>R <sub>G</sub> =1.7Ω, V <sub>GS</sub> =10V |     | 15   |      | nS   |
| Turn-on Rise Time                        | t <sub>r</sub>      |                                                                                           |     | 14   |      | nS   |
| Turn-Off Delay Time                      | t <sub>d(off)</sub> |                                                                                           |     | 72   |      | nS   |
| Turn-Off Fall Time                       | t <sub>f</sub>      |                                                                                           |     | 14   |      | nS   |
| Source- Drain Diode Characteristics      |                     |                                                                                           |     |      |      |      |
| Source-drain current(Body Diode)         | I <sub>SD</sub>     | T <sub>C</sub> =25℃                                                                       |     |      | 36   | A    |
| Pulsed Source-drain current(Body Diode)  | I <sub>SDM</sub>    |                                                                                           |     |      | 108  | A    |
| Forward On Voltage                       | V <sub>SD</sub>     | T <sub>J</sub> =25℃, I <sub>SD</sub> =36A, V <sub>GS</sub> =0V                            |     | 1.0  | 1.2  | V    |
| Reverse Recovery Time                    | t <sub>rr</sub>     | T <sub>J</sub> =25℃, I <sub>F</sub> =18A, di/dt=100A/μs                                   |     | 160  |      | nS   |
| Reverse Recovery Charge                  | Q <sub>rr</sub>     |                                                                                           |     | 0.96 |      | uC   |
| Peak Reverse Recovery Current            | I <sub>rrm</sub>    |                                                                                           |     | 12   |      | A    |

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature

2.  $T_J=25^\circ C, V_{DD}=50V, V_G=10V, R_G=25\Omega$

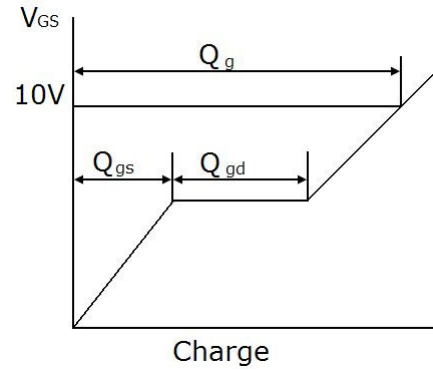
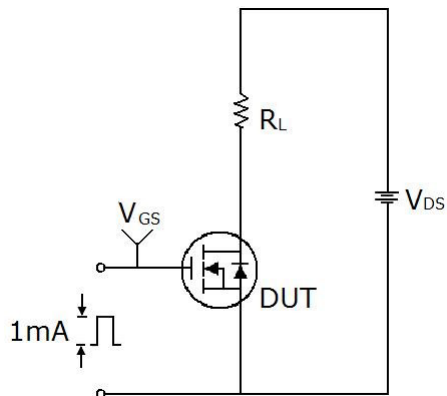
## TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (curves)

**Figure1. Safe operating area**

**Figure2. Capacitance**

**Figure3. Output characteristics**

**Figure4. Source-Drain Diode Forward Voltage**

**Figure5. Static drain-source on resistance**

**Figure6. Transfer characteristics**


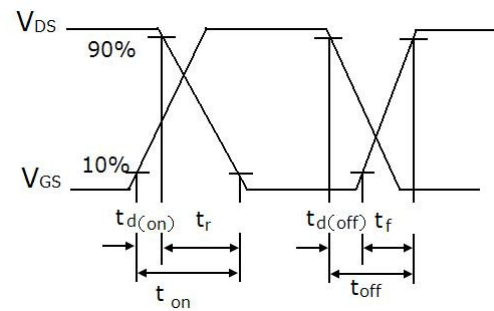
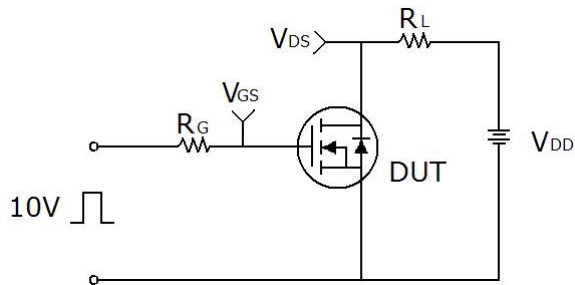
**Figure7.  $R_{DS(ON)}$  vs Junction Temperature**

**Figure8.  $BV_{DSS}$  vs Junction Temperature**

**Figure9. Gate charge waveforms**

**Figure10. Maximum  $I_D$  vs Junction Temperature**


## Test circuit

### 1) Gate charge test circuit & Waveform



### 2) Switch Time Test Circuit:



### 3) Unclamped Inductive Switching Test Circuit & Waveforms

